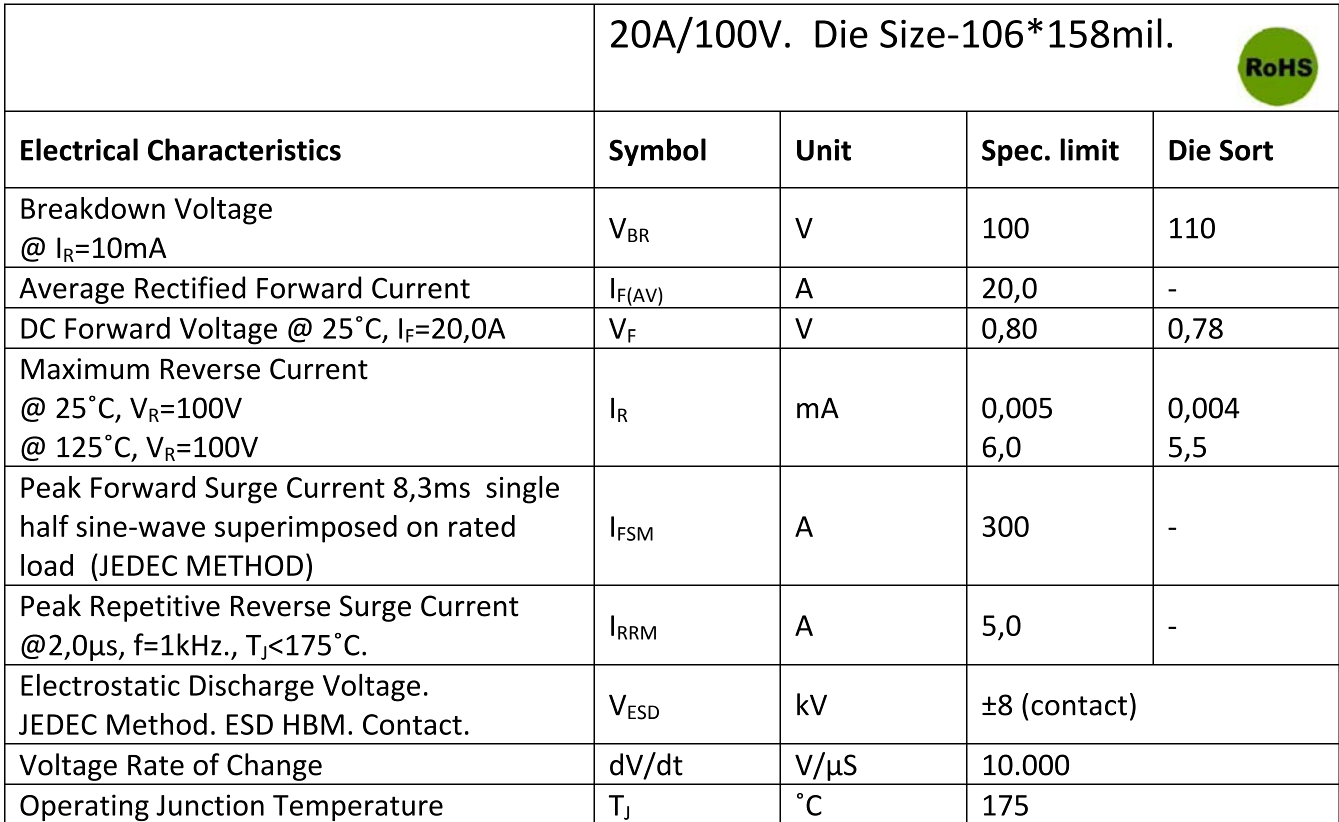
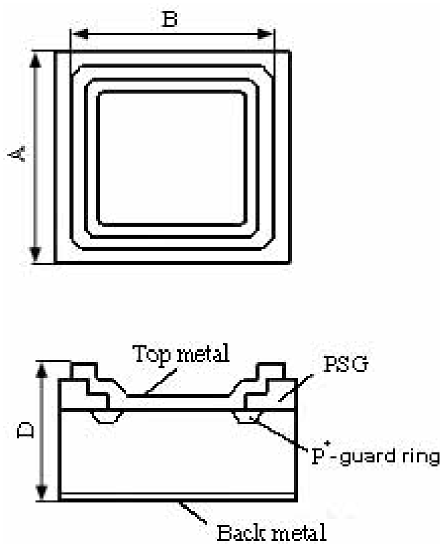


	20A/100V. Die Size-106*158mil. RoHS			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	100	110
Average Rectified Forward Current	$I_{F(AV)}$	A	20,0	-
DC Forward Voltage @ 25˚C, I_F=20,0A	V_F	V	0,80	0,78
Maximum Reverse Current @ 25˚C, V_R=100V @ 125˚C, V_R=100V	I_R	mA	0,005 6,0	0,004 5,5
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	300	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<175˚C.	I_{RRM}	A	5,0	-
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	V_{ESD}	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	175	



DIM	ITEM	µm
A_X A_y	Wafer Form Die Size	2700 4000
B_X B_y	Top Metal Size	2560 3860
D	Thickness	300max.
Scribe line Width		80

Top metal:
a) **Al-Ni-Ag** – for Soldering;
b) **Al** – for Wire Bonding.
Backside metal: **Ti-Ni-Ag**.